Method to pattern etch masks in two inclined planes for three-dimensional nano- and microfabrication

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In this article the author list is displayed in incorrect order. The correct order is R. Willem Tjerkstra, Léon A. Woldering, Johanna M. van den Broek, Fred Roozeboom, Irwan D. Setija, and Willem L. Vos. This is already corrected in the online version of the article.